

μPA2738GR

P-channel MOSFET

-30 V, -10 A, 15 mΩ

R07DS0870EJ0100

Rev.1.00

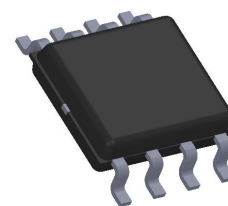
Aug 28, 2012

Description

The μPA2738GR is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

Features

- $V_{DSS} = -30\text{ V}$ ($T_A = 25^\circ\text{C}$)
- Low on-state resistance
— $R_{DS(on)} = 15\text{ m}\Omega\text{ MAX.}$ ($V_{GS} = -10\text{ V}$, $I_D = -10\text{ A}$)
- 4.5 V Gate-drive available
- Small and surface mount package (Power SOP8)
- Pb-free and Halogen free



Power SOP8

Ordering Information

| Part No. | LEAD PLATING | PACKING | Package |
|------------------|--------------|------------------|-------------|
| μ PA2738GR-E1-AT | Pure Sn | Tape 2500 p/reel | Power SOP8 |
| μ PA2738GR-E2-AT | | | 0.08 g TYP. |

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

| Item | Symbol | Ratings | Unit |
|---|----------------|-------------|------------------|
| Drain to Source Voltage ($V_{GS} = 0\text{ V}$) | V_{DSS} | -30 | V |
| Gate to Source Voltage ($V_{DS} = 0\text{ V}$) | V_{GSS} | ± 20 | V |
| Drain Current (DC) | $I_{D(DC)}$ | ± 10 | A |
| Drain Current (pulse) *1 | $I_{D(pulse)}$ | ± 100 | A |
| Total Power Dissipation *2 | P_{T1} | 1.1 | W |
| Total Power Dissipation (PW = 10 sec) *2 | P_{T2} | 2.5 | W |
| Channel Temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| Single Avalanche Current *3 | I_{AS} | 10 | A |
| Single Avalanche Energy *3 | E_{AS} | 10 | mJ |

Thermal Resistance

Channel to Ambient Thermal Resistance *2 $R_{th(ch-A)}$ 114 $^\circ\text{C/W}$

Notes: *1. $PW \leq 10\ \mu\text{s}$, Duty Cycle $\leq 1\%$

*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm

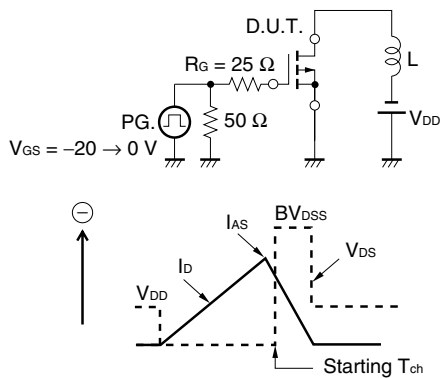
*3. Starting $T_{ch} = 25^\circ\text{C}$, $V_{DD} = -15\text{ V}$, $R_G = 25\ \Omega$, $V_{GS} = -20 \rightarrow 0\text{ V}$, $L = 100\ \mu\text{H}$

Electrical Characteristics (T_A = 25°C)

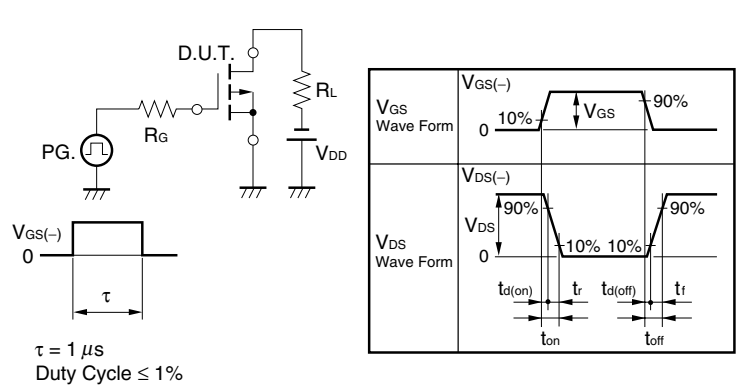
| Item | Symbol | MIN. | TYP. | MAX. | Unit | Test Conditions |
|--|----------------------|------|------|------|------|--|
| Zero Gate Voltage Drain Current | I _{DSS} | | | -1 | μA | V _{DS} = -30 V, V _{GS} = 0 V |
| Gate Leakage Current | I _{GSS} | | | ±100 | nA | V _{GS} = ±20 V, V _{DS} = 0 V |
| Gate Cut-off Voltage | V _{GS(off)} | -1.0 | | -2.5 | V | V _{DS} = -10 V, I _D = -1 mA |
| Forward Transfer Admittance *1 | y _{fs} | 4 | | | S | V _{DS} = -10 V, I _D = -5.0 A |
| Drain to Source On-state Resistance *1 | R _{DS(on)1} | | 12 | 15 | mΩ | V _{GS} = -10 V, I _D = -10 A |
| | R _{DS(on)2} | | 19 | 29 | mΩ | V _{GS} = -4.5 V, I _D = -10 A |
| Input Capacitance | C _{iSS} | | 1450 | | pF | V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz |
| Output Capacitance | C _{oSS} | | 710 | | pF | |
| Reverse Transfer Capacitance | C _{rSS} | | 650 | | pF | |
| Turn-on Delay Time | t _{d(on)} | | 14 | | ns | V _{DD} = -15 V, I _D = -5.0 A, V _{GS} = -10 V, R _G = 10 Ω |
| Rise Time | t _r | | 30 | | ns | |
| Turn-off Delay Time | t _{d(off)} | | 60 | | ns | |
| Fall Time | t _f | | 50 | | ns | |
| Total Gate Charge | Q _G | | 37 | | nC | V _{DD} = -24 V, V _{GS} = -10 V, I _D = -10 A |
| Gate to Source Charge | Q _{GS} | | 2.5 | | nC | |
| Gate to Drain Charge | Q _{GD} | | 20 | | nC | |
| Body Diode Forward Voltage *1 | V _{F(S-D)} | | 0.86 | | V | I _F = 10 A, V _{GS} = 0 V |
| Reverse Recovery Time | t _{rr} | | 47 | | ns | I _F = 10 A, V _{GS} = 0 V, di/dt = 100 A/μs |
| Reverse Recovery Charge | Q _{rr} | | 43 | | nC | |

Note: *1. Pulsed

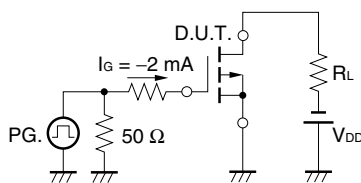
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

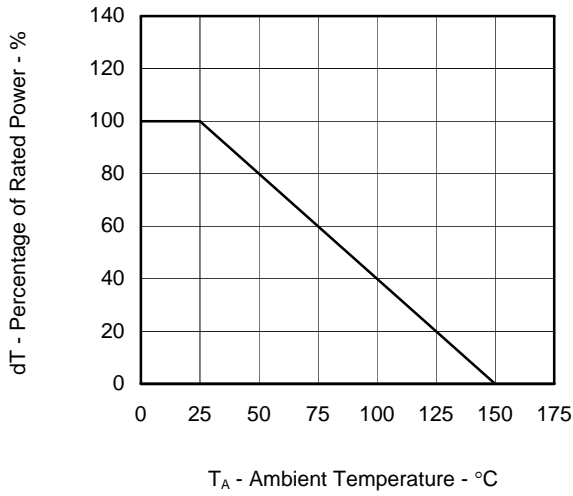


TEST CIRCUIT 3 GATE CHARGE

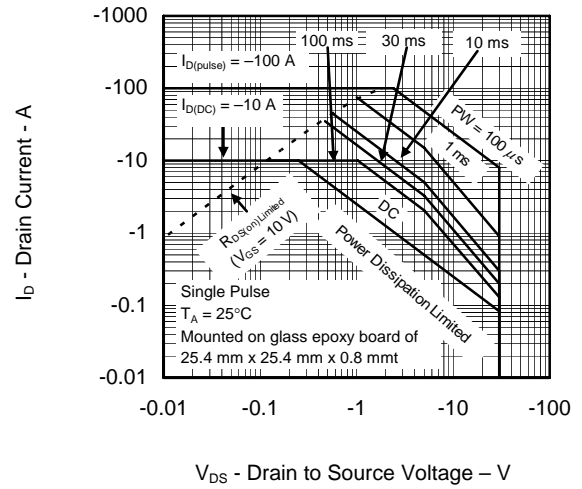


TYPICAL CHARACTERISTICS (T_A = 25°C)

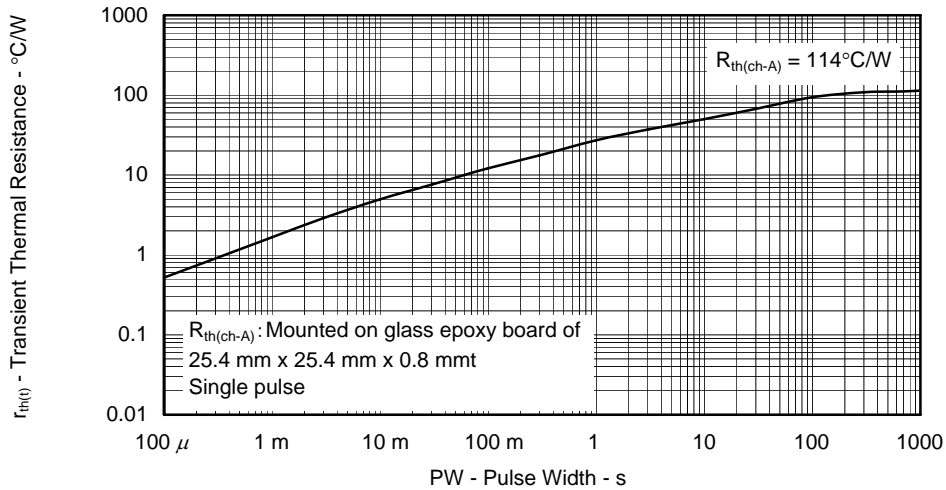
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



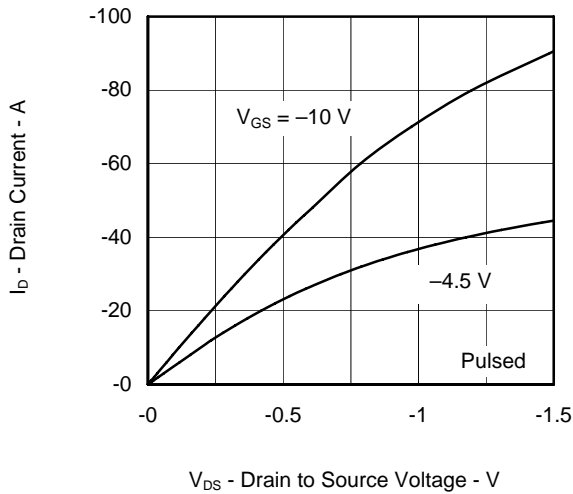
FORWARD BIAS SAFE OPERATING AREA



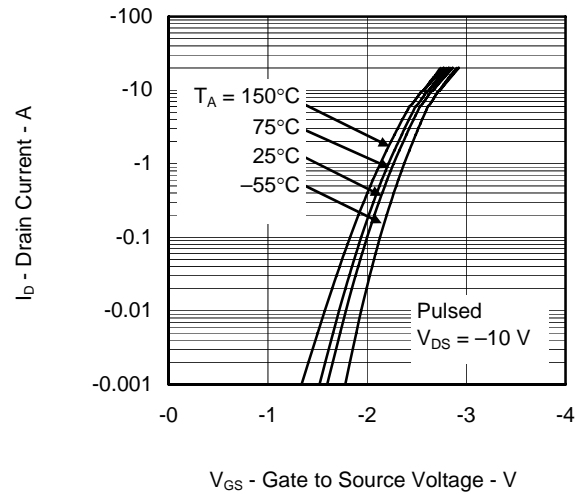
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



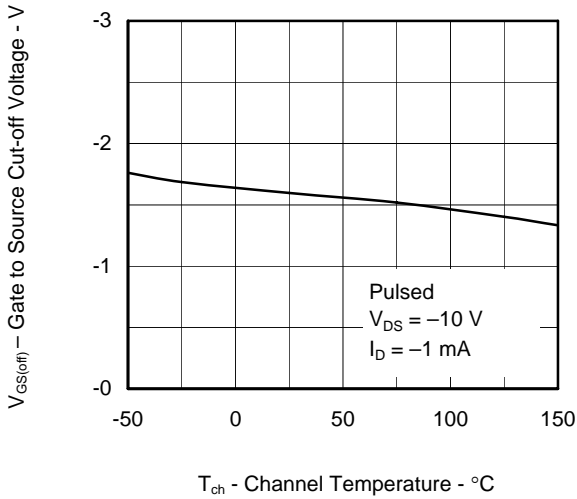
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



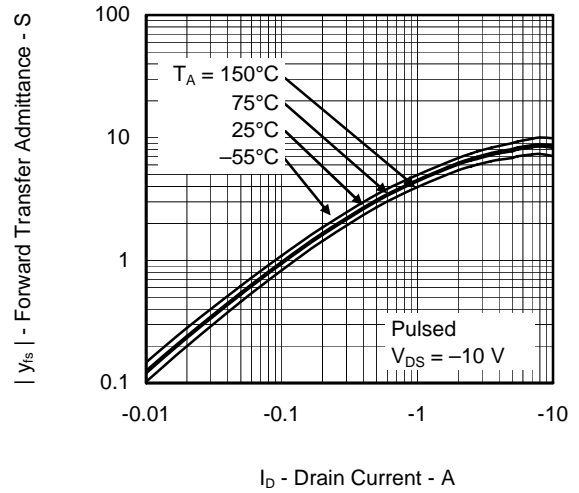
FORWARD TRANSFER CHARACTERISTICS



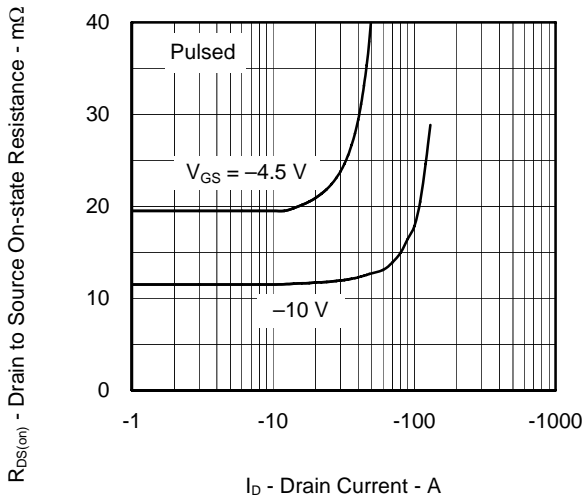
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



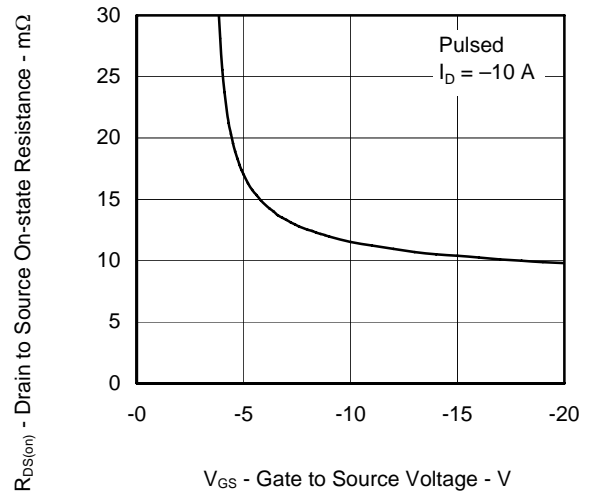
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



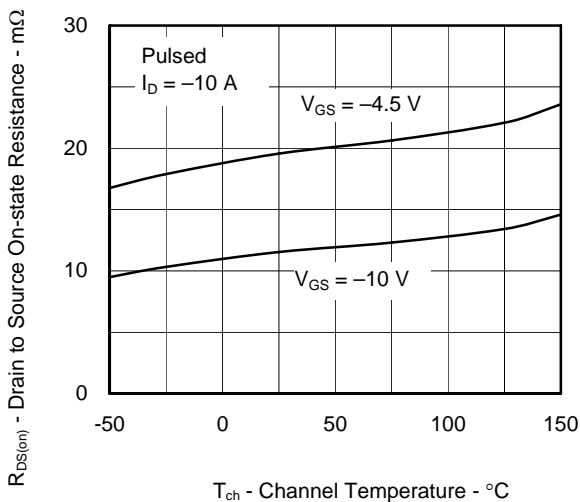
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



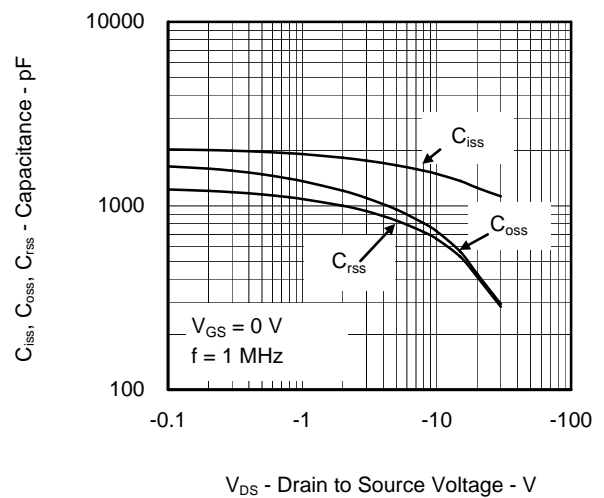
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



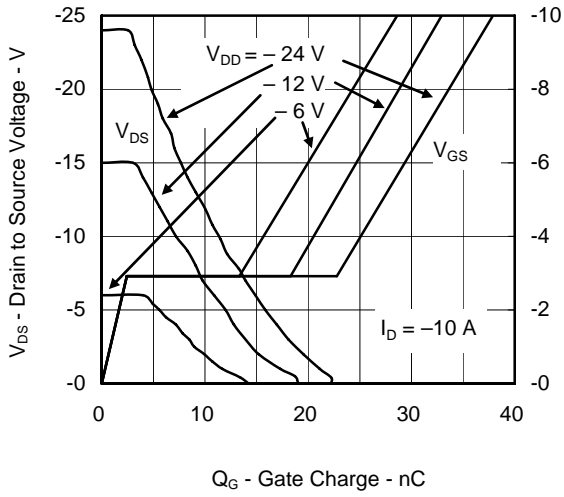
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



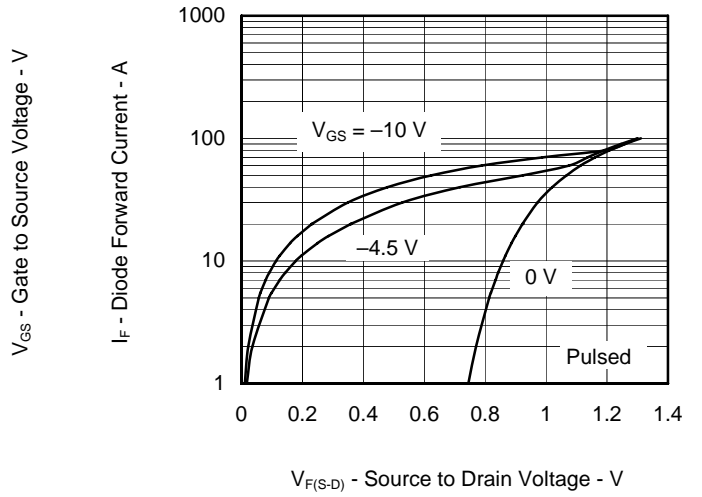
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS

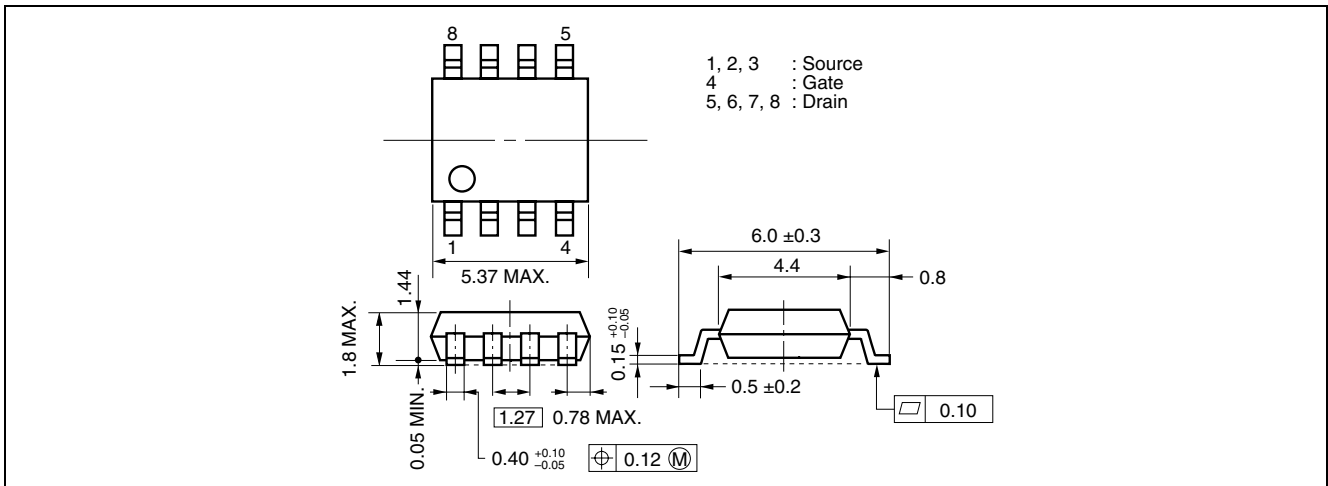


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

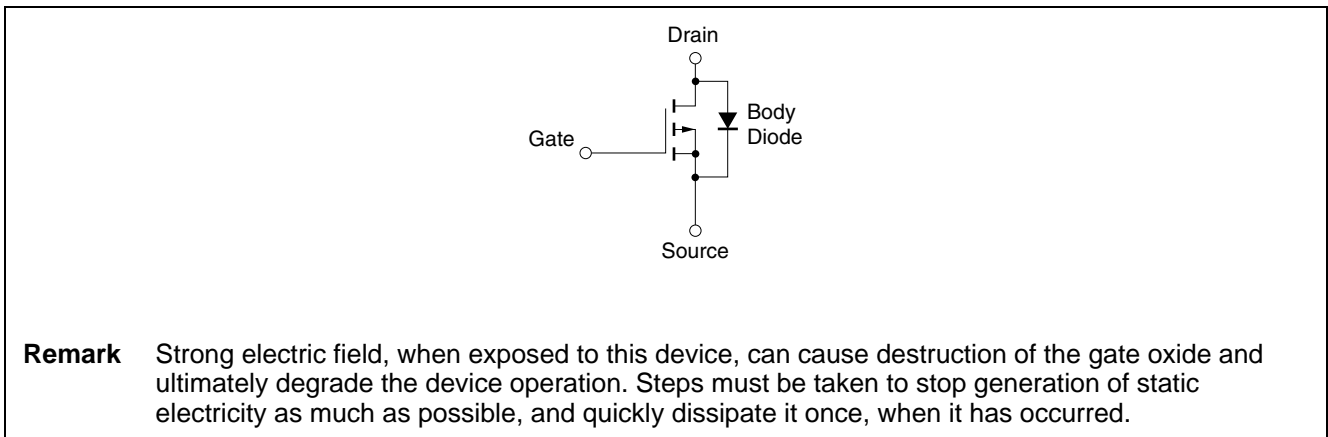


Package Drawings (Unit: mm)

Power SOP8



Equivalent Circuit



| | |
|-------------------------|-----------------------------|
| Revision History | μPA2738GR Data Sheet |
|-------------------------|-----------------------------|

| Rev. | Date | Description | |
|------|--------------|-------------|----------------------|
| | | Page | Summary |
| 1.00 | Aug 28, 2012 | - | First Edition Issued |

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
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Renesas Electronics Korea Co., Ltd.
11F., Samik Laviel' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141